

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Wilk *et al.*

Serial No.: 09/176,422

Filed: 10/21/98

For: Low Temperature Method for Forming a Thin, Uniform Oxide



Docket: TI-24742

Examiner: N. Berezny

Art Unit: 2823

6/13/00  
9/29/00

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**REPLY PURSUANT TO 37 C.F.R. § 1.111**

August 21, 2000

Ass't Commissioner for Patents  
Washington, DC 20231

Examiner:

In response to the Office Action dated April 20, 2000, please amend the above-identified patent application as follows:

**IN THE TITLE:**

Please

**IN THE SPECIFICATION:**

Top of page 1, please change:

"This application claims the benefit of priority from the following U.S. applications:

Filing

Date	Appl. #	Title
7/31/97	08/904,009	Method For Thin Film Deposition On Single-Crystal Semiconductor Substrates
10/23/97	60/063,010	Low Temperature Method for Forming a Thin, Uniform Oxide"

to

--This application is a continuation-in-part of application 08/904,009, titled Method For Thin Film Deposition On Single-Crystal Semiconductor Substrates, filed 7/31/97. This application claims the